

N-Channel 100 V (D-S) MOSFET



RoHS
COMPLIANT

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A) ^a	Q _g (Typ.)
100	125 at V _{GS} = 10 V	3	18.5 nC
	130 at V _{GS} = 4.5 V		

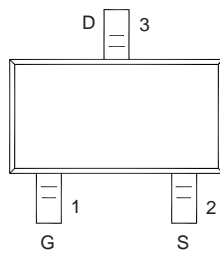
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Optimized for fast-switching applications

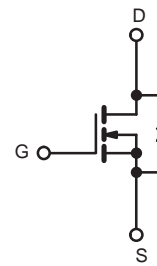
APPLICATIONS

- Synchronous Rectification
- Isolated DC/DC Converters in Telecom and Industrial

(SOT-23-3L)



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _C = 25 °C	3
		T _C = 100 °C	1.8
Pulsed Drain Current ^b	I _{DM}	12	A
Maximum Power Dissipation ^c	P _D	T _C = 25 °C	3
		T _C = 100 °C	1.28
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to +150	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	MAX	UNIT
Junction-to-Ambient (PCB Mount) ^d	R _{thJA}	120	°C/W
Junction-to-Case (Drain)	R _{thJC}	39	

Notes

- Calculated continuous current based on maximum allowable junction temperature.
- Repetitive rating; pulse width limited by max. junction temperature.
- P_d is based on max. junction temperature, using junction-case thermal resistance.
- The value of R_{thJA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 °C.

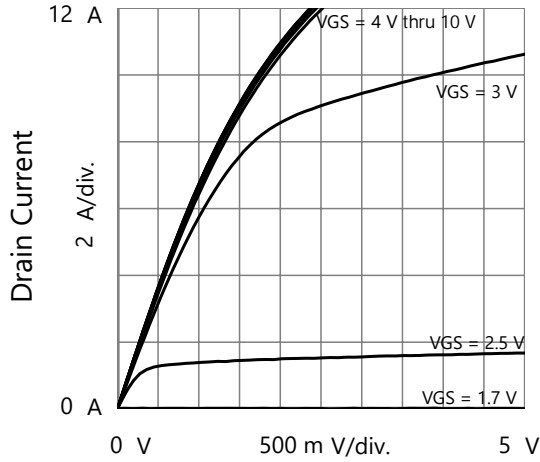
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$	100			V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		3	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 4.5\text{ V}$	3			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 2\text{ A}$		125	150	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 2\text{ A}$		130	160	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 5\text{ V}, I_D = 2\text{ A}$		5		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1040		pF
Output Capacitance	C_{oss}			23		
Reverse Transfer Capacitance	C_{rss}			17		
Total Gate Charge	Q_g	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 2\text{ A}$		18.5		nC
Gate-Source Charge	Q_{gs}			2		
Gate-Drain Charge	Q_{gd}			2.5		
Gate Resistance	R_g	$f = 1\text{ MHz}$		2.1		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 25\text{ }\Omega$ $I_D \cong 2\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		8		ns
Rise Time	t_r			6		
Turn-Off Delay Time	$t_{d(off)}$			23		
Fall Time	t_f			5		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			3	A
Pulse Diode Forward Current	I_{SM}				12	
Body Diode Voltage	V_{SD}	$I_S = 1\text{ A}$			1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 2\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		15		ns
Body Diode Reverse Recovery Charge	Q_{rr}				30	

Notes:

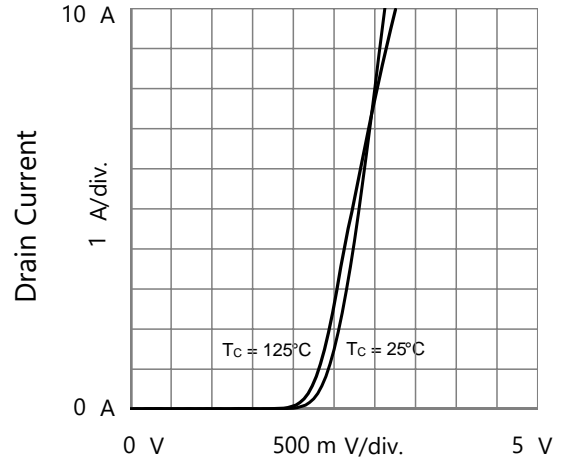
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

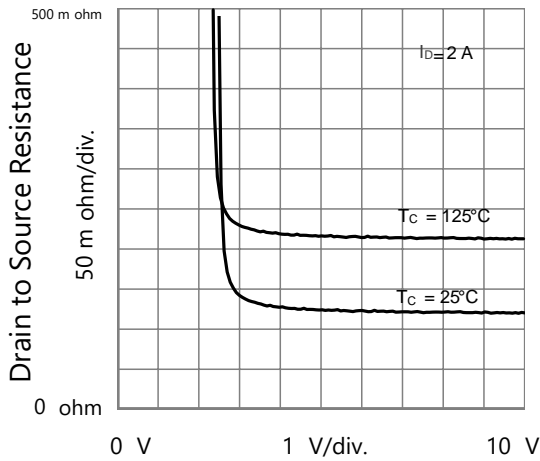
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



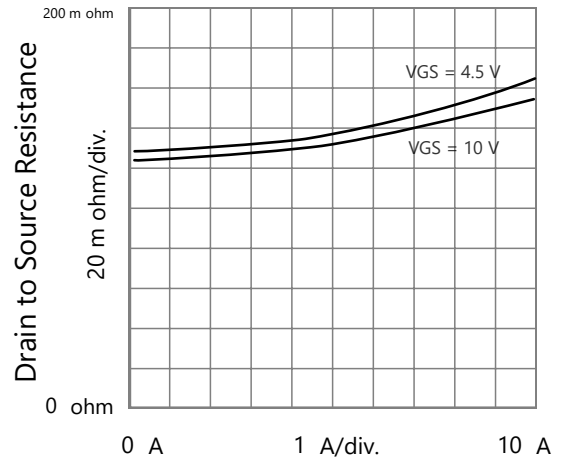
Drain to Source Voltage
Output Characteristics



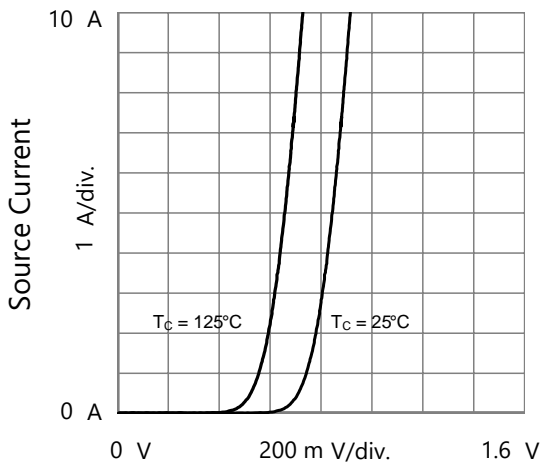
Gate to Source Voltage
Transfer Characteristics



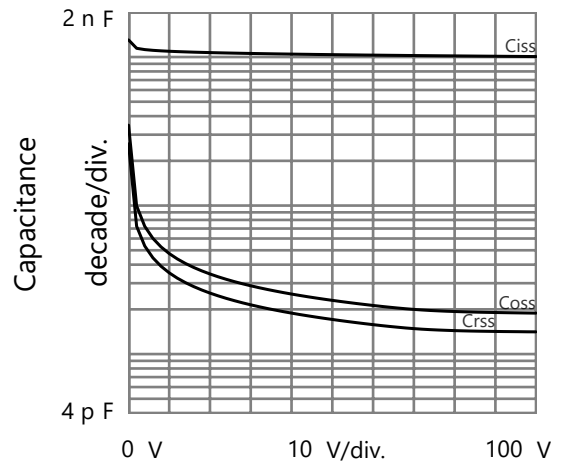
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



Drain Current
Drain to Source Resistance vs. Drain Current

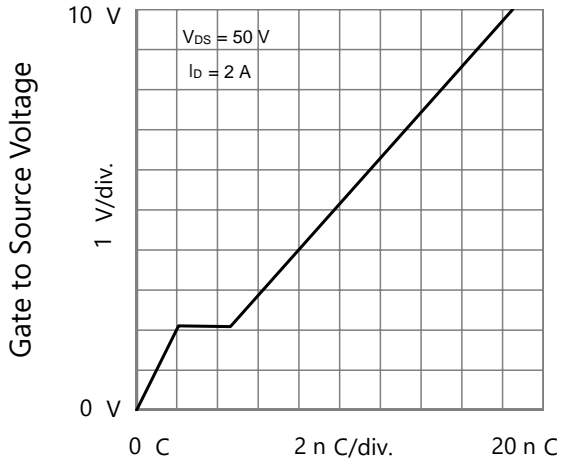


Source to Drain Voltage
Body Diode Forward Characteristics

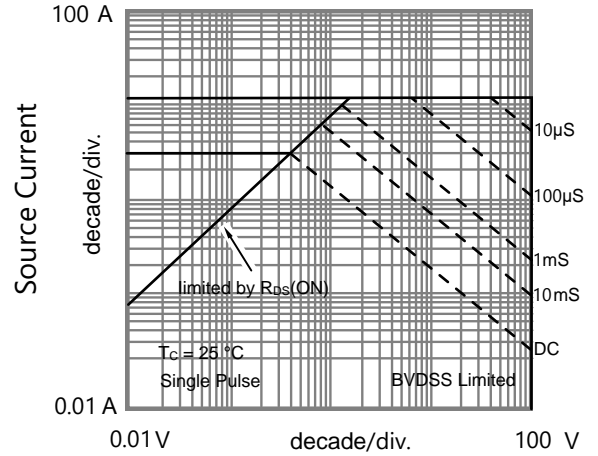


Drain to Source Voltage
Capacitances

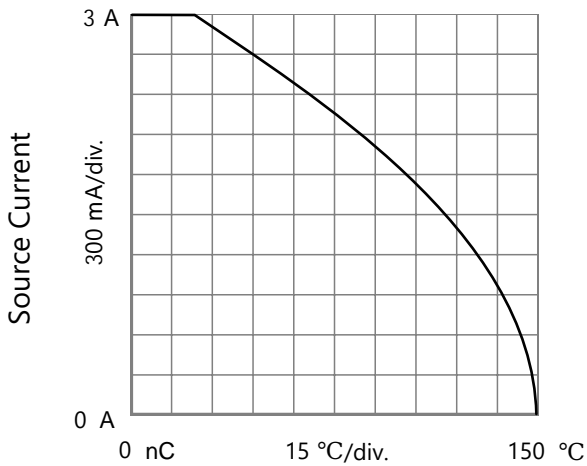
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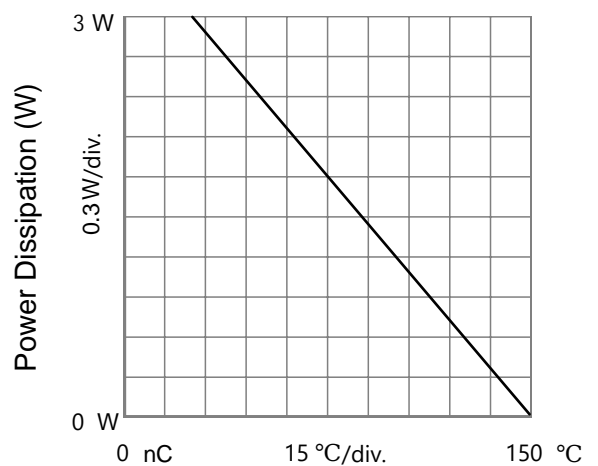
Gate Charge
Gate to Source Voltage vs. Gate Charge



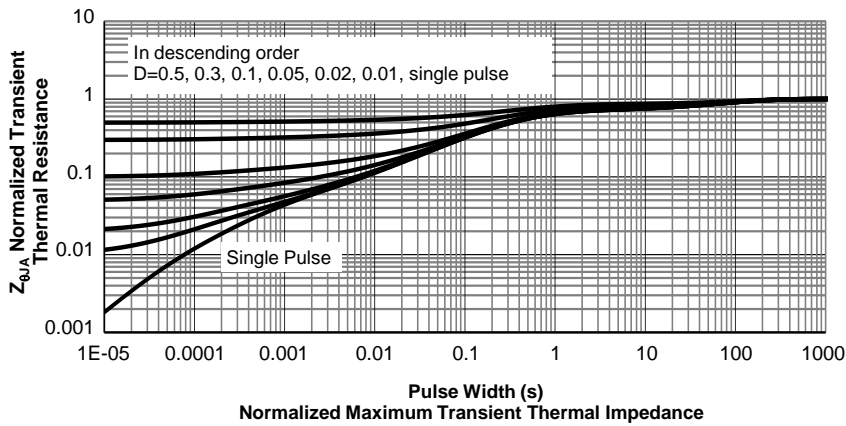
Source to Drain Voltage
Safe Operating Area, Junction-to-Ambient



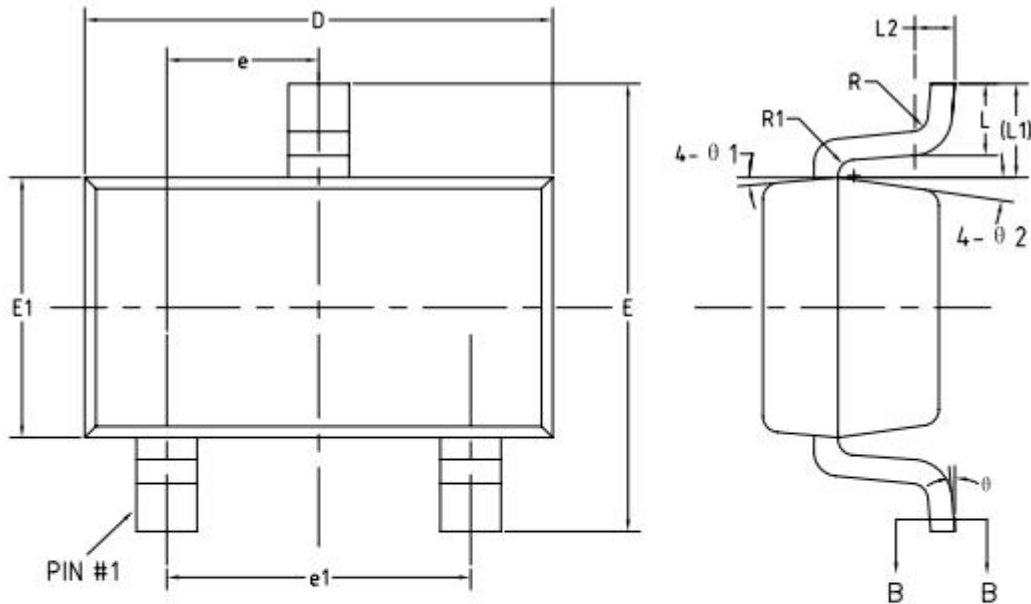
T_C - Case Temperature



T_C - Case Temperature



SOT-23-3L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX
A	-	-	1.50
A1	0.00	-	0.18
A2	0.85	1.10	1.35
A3	0.58	0.65	0.72
b	0.23	-	0.53
b1	0.20	0.40	0.50
c	0.09	-	0.22
c1	0.08	0.13	0.21
D	2.78	2.95	3.10
E	2.58	2.80	3.03
E1	1.55	1.65	1.78
e	0.83	0.95	1.07
e1	1.78	1.90	2.02
L	0.28	0.45	0.62
L1	0.59REF		
L2	0.25BSC		
R	0.04	-	-
R1	0.04	-	0.21
θ	0°	-	8°
θ1	8°	10°	12°
θ2	8°	10°	12°

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